

## AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A method for forming a photoresist pattern comprising:

(a) preparing a gas protection composition comprising a water-soluble polymer selected from the group consisting of copolymers of methyl methacrylate and acrylic acid, copolymers of methyl acrylate and acrylic acid, and mixtures thereof;

~~(a) coating~~ (b) forming an etching mask layer on an underlying layer;

~~(b) coating~~ (c) applying a photoresist composition including silicon on the etching mask layer to form a photoresist film, ~~the photoresist film generating silicon gas upon exposure to light in part (d) below;~~

~~(e) (d) applying the gas protection composition on the photoresist film, thereby forming a gas protection film comprising a water-soluble polymer material on the photoresist film, the gas protection film absorbing silicon gas generated from the photoresist film during an exposure process;~~

~~(d) (e)~~ performing a photolithography process on the resulting structure to form a photoresist film pattern;

~~(e) (f)~~ etching the etching mask layer of step ~~(a)~~ (b) using the photoresist film pattern as an etching mask to form an etching mask pattern; and,

~~(f) (g)~~ forming an underlying layer pattern by an etching process using the etching mask pattern.

2. (Currently Amended) The method according to claim 1, comprising forming the etching mask layer of ~~part~~ step (a) by coating an i-line photoresist or KrF photoresist.

3. (Canceled)

4. (Previously Presented) The method according to claim 1, wherein the photoresist composition is suitable for a photolithographic process employing a light source selected from the group consisting of ArF (193nm), VUV (157nm) and EUV (13nm).

5. (Canceled)

6. (Canceled).

7. (Currently Amended) The method according to claim 1, wherein the light is photolithography process employs a light source selected from the group consisting of ArF (193nm), VUV (157nm) ~~or~~ and EUV (13nm).

8. (Currently Amended) The method according to claim 1, wherein ~~part (e)~~ step (d) further comprises:

~~(e-1)~~ (d-1) spin coating a the gas protection composition on the resultant surface of ~~(b)~~ step (c); and,

~~(e-2)~~ (d-2) baking the coated gas protection composition.

9. – 13. (Canceled)